



SSCN3904GS7

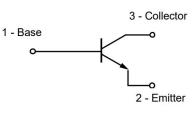
NPN Switching Transistor

> Features

VCB	VCE VBE		VCESAT	IC	
60V	40V	6V	300mV	200mA	

> Description

The NPN Transistor is designed for use in linear and switching applications. The device is housed in the SOT-323 package, which is designed for telephony and professional communication equipment.



SOT-323

Pin configuration

 \geq



Applications

- General purpose switching and amplification
- Telephony and professional communication equipment

> Ordering Information

Device	Package	Shipping		
SSCN3904GS7	SOT-323	3000/Reel		





SSCN3904GS7

> Absolute Maximum Ratings($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector- Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Collector Current-Continuous	lc	200	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55 to 150	°C

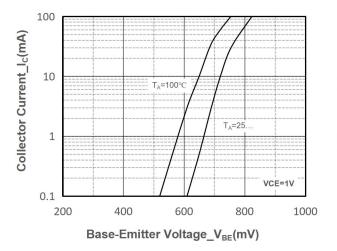
> Electrical Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

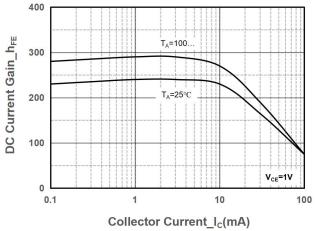
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =10uA,I _E =0	60			V
Collector-emitter Breakdown Voltage	BV _{CEO}	I _C =1mA,I _B =0	40			V
Emitter -Base Breakdown Voltage	BV _{EBO}	I _E =10uA,I _C =0	6			V
Collector Cutoff Current	ICEX	V _{CE} =30V, V _{EB} =3V			50	nA
Collector Cutoff Current	I _{CBO}	V _{CB} =30V,I _E =0			100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =3V,I _C =0			100	nA
	h _{FE}	V _{CE} =1V,I _C =10mA	100		300	
DC Current Gain		V _{CE} =1V,I _C =0.1mA	40			
		V _{CE} =1V,I _C =100mA	30			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =50mA,I _B =5mA			0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	Ic=50mA,I _B =5mA			0.95	V
Transition frequency	fT	V _{CE} =20V,I _C =10mA f=100MHz	250			MHz
Delay Time	ta	V _{CC} =3V,V _{BE(off)} =-0.5V I _C =10mA,I _{B1} =1mA			35	ns
Rise Time	tr	$V_{CC}=3V, V_{BE(off)}=-0.5V$ $I_{C}=10mA, I_{B1}=1mA$			35	ns
Storage Time	ts	V _{CC} =3V,I _C =10mA		2	200	ns
		I _{B1} = I _{B2} =1mA			200	
Fall Time	+	V _{CC} =3V,I _C =10mA			50	ns
	t _f	I _{B1} = I _{B2} =1mA				



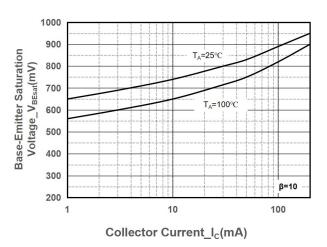
SSCN3904GS7

> Typical Performance Characteristics (T_A=25°C unless otherwise noted)

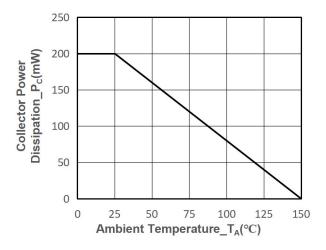




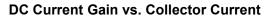
Collector Current vs. Base-Emitter Voltage

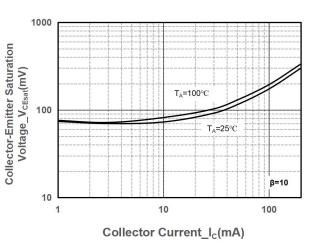




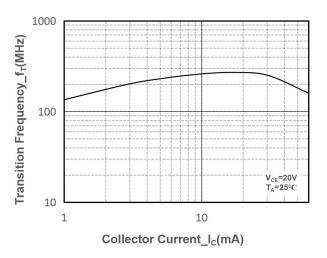








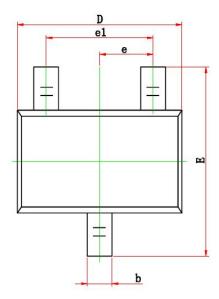
V_{CE(sat)} vs. Collector Current

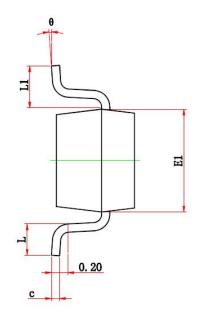


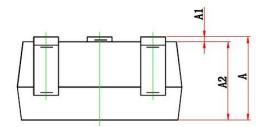
Transition Frequency vs. Collector Current



Package Information







Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	2.150	2.450	0.085	0.096	
E1	1.150	1.350	0.045	0.053	
e	0.650 TYP.		0.026 TYP.		
e1	1.200	1.400	0.047	0.055	
L	0.260	0.460	0.010	0.018	
L1	0.525 REF.		0.021 REF.		
θ	0 °	8°	0°	8°	



DISCLAIMER

SSCSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. SSCSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICIENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G,. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.

OUR PRODUCT SPECIFICATIONS ARE ONLY VALID IF OBTAINED THROUGH THE COMPANY'S OFFICIAL WEBSITE, CRM SYSTEM, OR OUR SALES PERSONNEL CHANNELS. IF CHANGES OR SPECIAL VERSIONS ARE INVOLVED, THEY MUST BE STAMPED WITH A QUALITY SEAL AND MARKED WITH A SPECIAL VERSION NUMBER TO BE VALID.